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January 2008

FDC855N

Single N-Channel, Logic Level, PowerTrench® MOSFET 30V, 6.1A, 27m Ω

Features

- Max $r_{DS(on)} = 27m\Omega$ at $V_{GS} = 10V$, $I_D = 6.1A$
- Max $r_{DS(on)} = 36m\Omega$ at $V_{GS} = 4.5V$, $I_D = 5.3A$
- SuperSOTTM -6 package: small footprint (72% smaller than standard SO-8; low profile (1mm thick).
- RoHS Compliant

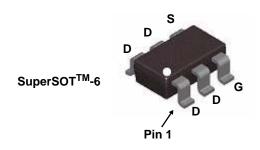


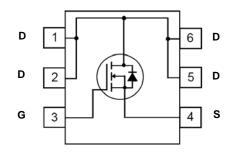
General Description

This N-Channel Logic Level MOSFET is an efficient solution for low voltage and battery powered applications. Utilizing Fairchild Semiconductor's advanced PowerTrench® process, this device possesses minimized on-state resistance to optimize the power consumption. They are ideal for applications where in-line power loss is critical.

Application

■ Power Management in Notebook, Hard Disk Drive





MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Parameter		
V_{DS}	Drain to Source Voltage		30	V
V_{GS}	Gate to Source Voltage	±20	V	
	Drain Current -Continuous T _A = 25°C	(Note 1a)	6.1	۸
'D	-Pulsed		20	- A
В	Power Dissipation (Steady State)	(Note 1a)	1.6	W
P_{D}	Power Dissipation (Steady State)	(Note 1b)	0.8	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range	Operating and Storage Junction Temperature Range		°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	30	°C/\\/
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.855	FDC855N	SuperSOT-6	7"	8 mm	3000 units

Units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted Parameter

Off Char	acteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 2	5°C	24		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V$, $V_{DS} = 24V$, $T_{C} =$	125°C		1 250	μА
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			±100	nA

Test Conditions

Min

Тур

Max

On Characteristics

Symbol

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.0	2.0	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-6		mV/°C
		$V_{GS} = 10V, I_D = 6.1A$		20.7	27.0	
r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 5.3A$		28.2	36.0	mΩ	
		$V_{GS} = 10V$, $I_D = 6.1A$, $T_J = 125$ °C		30.1	39.3	
g _{FS}	Forward Transconductance	$V_{DD} = 10V, I_D = 6.1A$		20		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 45V V 0V	493	655	pF
C _{oss}	Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1MHz	108	145	pF
C _{rss}	Reverse Transfer Capacitance	1 - 11/11/2	62	95	pF
R_q	Gate Resistance	f = 1MHz	1.0		Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	.,	6	12	ns
t _r	Rise Time	$V_{DD} = 15V, I_D = 6.1A,$ $V_{GS} = 10V, R_{GEN} = 6\Omega$	2	10	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = 10V, K _{GEN} = 652	14	23	ns
t _f	Fall Time		2	10	ns
Q_g	Total Gate Charge at 10V	V _{GS} =0Vto10V	9.2	13	nC
Qg	Total Gate Charge at 5V	$V_{GS} = 0V \text{ to } 5V$ $V_{DD} = 15V,$ $I_{D} = 6.1A$	4.9	7.0	nC
Q _{gs}	Gate to Source Charge	I _D = 0.1A	1.7		nC
Q _{gd}	Gate to Drain "Miller" Charge		3.1		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_S = 1.3A$ (Note 2)		0.80	1.2	V
t _{rr}	Reverse Recovery Time	I _E = 6.1A, di/dt = 100A/μs		17	31	ns
Q _{rr}	Reverse Recovery Charge	I _F = 6.1A, di/dt = 100A/μS		6	12	nC

^{1:} R_{0JA} is the sum of the junction-to-case and case-to- ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 78°C/W when mounted on a 1 in² pad of 2 oz copper.



b. 156°C/W when mounted on a minimum pad of 2 oz copper.

^{2:} Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%.

Typical Characteristics T_J = 25°C unless otherwise noted

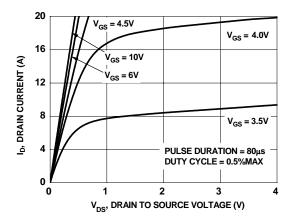


Figure 1. On-Region Characteristics

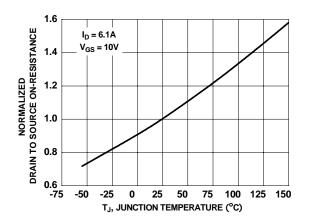


Figure 3. Normalized On-Resistance vs Junction Temperature

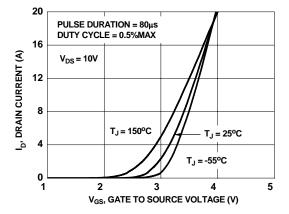


Figure 5. Transfer Characteristics

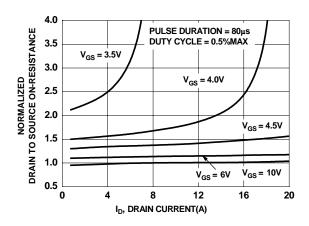


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

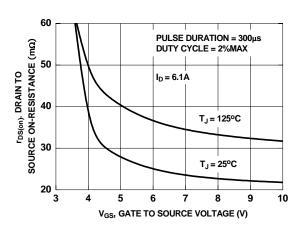


Figure 4. On-Resistance vs Gate to Source Voltage

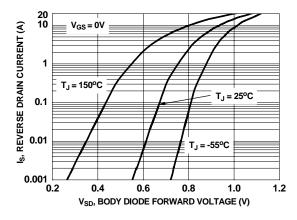


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

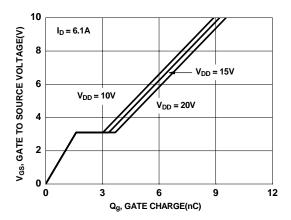


Figure 7. Gate Charge Characteristics

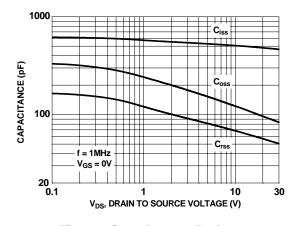


Figure 8. Capacitance vs Drain to Source Voltage

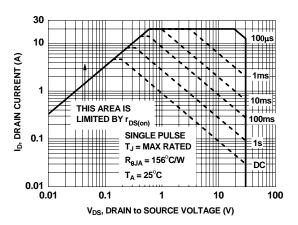


Figure 9. Forward Bias Safe Operating Area

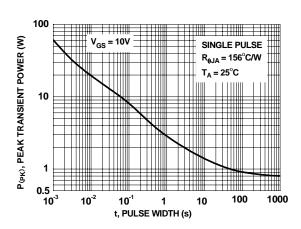


Figure 10. Single Pulse Maximum Power Dissipation

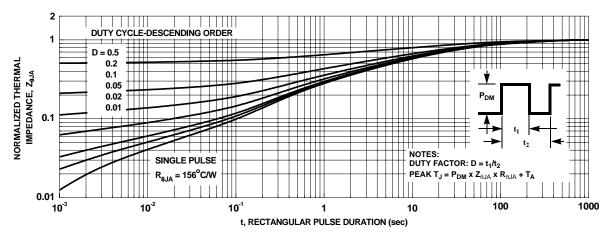
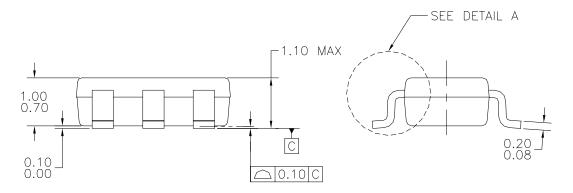
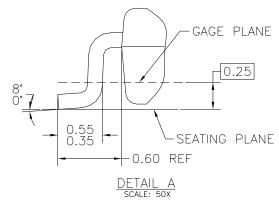


Figure 11. Transient Thermal Response Curve

Dimensional Outline and Pad Layout SYMM É 0.95 -0.953.00 2.80 ► A 1.00 MIN 6 4 B 3.00 2.60 2.60 1.70 1.50 3 0.50 0.30 0.95 ◆ 0.20 M C A B 0.70 MIN + 1.90 LAND PATTERN RECOMMENDATION (0.30) —





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NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO JEDEC MO-193. VAR. AA, ISSUE C, DATED JANUARY 2000.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.





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